

June 2008

Revision:A

SEBT818BA

HIGH GAIN LOW VOLTAGE PNP POWER TRANSISTOR

DESCRIPTION

The device is manufactured in low voltage PNP Planar Technology by using a "Base Island" layout.

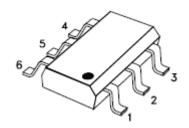
The resulting Transistor shows exceptional high gain performance coupled with very low saturation voltage

Features

- VERY LOW COLLECTOR EMITTER SATURATION VOLTAGE
- DC CURRENT GAIN>100(hpe)
- 3 A CONTINUOUS COLLECTOR CURRENT(I_C)
- SURFACE-MOUNTING SOT23-5L
 PACKAGE IN TAPE & REEL

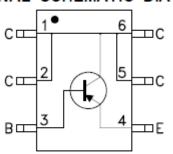
APPLICATIONS

- POWER MANAGEMENT IN PORTABLE EQUIPMENTS
- SWITCHING REGULATOR IN BATTERY CHARGER APPLICATIONS



SOT23-6L (TSOP6)

INTERNAL SCHEMATIC DIAGRAM



Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|-------------------------------------|---------------------------|------------|------|
| Collector-Base Voltage (IE = 0) | V _{CBO} | -30 | V |
| Collector-Emitter Voltage (IB = 0) | V _{CEO} | -30 | V |
| Emitter-Base Voltage (IC = 0) | V _{EBO} -5 | | V |
| Collector Current | I _C -3 | | А |
| Collector Peak Current | I _{CM} | -6 | А |
| Base Current | I _B | -0.2 | А |
| Base Peak Current | I _{BM} -(| | Α |
| Total Dissipation at TC = 25 oC | 5 oC P _{tot} 1.2 | | W |
| Storage Temperature | T _{stg} | -65 to 150 | °C |
| Max. Operating Junction Temperature | T _j | 150 | °C |

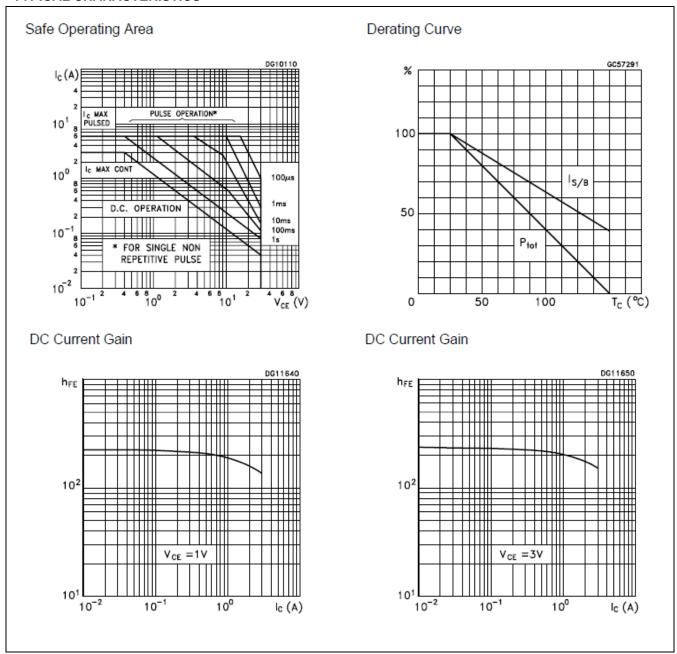
SEBT818BA

THERMAL DATA

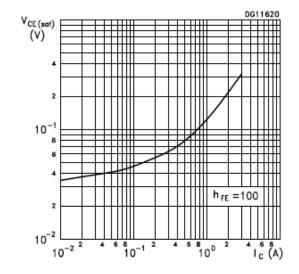
| R _{thj-amb} \'' I hermal Resistance Junction-ambient Max 104.2 °C/W | | | Thermal Resistance Junction-ambient | Max | | °C/W |
|--|--|--|-------------------------------------|-----|--|------|
|--|--|--|-------------------------------------|-----|--|------|

| Electric | Electrical Characteristics | | | | | | |
|------------------------|--|---|------------|-----------------|------------------------|--------------------------|--|
| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit | |
| I _{CBO} | Collector Cut-off Current (IE = 0) | $V_{CB} = -30 \text{ V}$ $V_{CB} = -30 \text{ V T}_{C} = 125 ^{\circ}\text{C}$ | | | -0.1 -20 | μ Α μ Α | |
| I _{EBO} | Emitter Cut-off Current (IC = 0) | V _{EB} = -5 V | | | -0.1 | μΑ | |
| V _{(BR)CEO*} | Collector-Emitter Breakdown Voltage (IB = 0) | ,I _C = -10 mA | -30 | | | V | |
| $V_{\text{CE(sat)}^*}$ | Collector-Emitter Saturation Voltage | $I_C = -0.5 \text{ A } I_B = -5 \text{ mA}$ $I_C = -2 \text{ A } I_B = -20 \text{ mA}$ $I_C = -1.2 \text{ A } I_B = -20 \text{ mA}$ | | -0.075 -0.21 | -0.15 -0.5 -0.25 | V V V | |
| V _{BE(sat)*} | Base-Emitter Saturation Voltage | $I_C = -0.5 \text{ A } I_B = -5 \text{ mA}$ $I_C = -1.2 \text{ A } I_B = -20 \text{ mA}$ $I_C = -2 \text{ A } I_B = -20 \text{ mA}$ | | -0.74 | -1.1 -1.1 -1.2 | V V V | |
| V _{BE(ON)*} | Base-Emitter Voltage | $I_{C} = -0.5 \text{ A V}_{CE} = -2 \text{ V}$ | | -0.71 | -1.1 | V | |
| h _{FE} ∗ | DC Current Gain | $I_{C} = -0.5 \text{ A V}_{CE} = -1 \text{ V}$ $I_{C} = -2.5 \text{ A V}_{CE} = -3 \text{ V}$ | 100 100 | | | | |

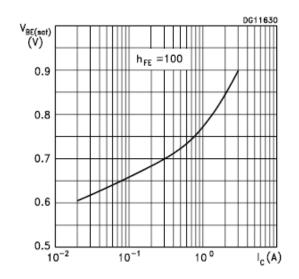
TYPICAL CHARACTERISTICS



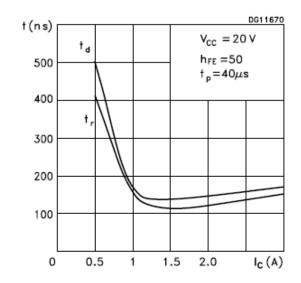
Collector-Emitter Saturation Voltage



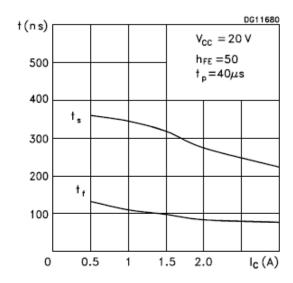
Base-Emitter Saturation Voltage



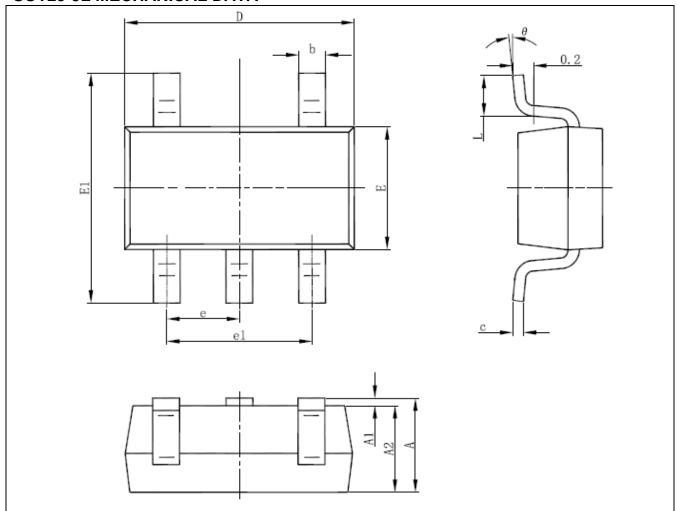
Switching Times Resistive Load



Switching Times Resistive Load



SOT23-5L MECHANICAL DATA



| Comb of | Dimensions In | Millimeters | In Inches | | |
|---------|---------------|-------------|------------|-------|--|
| Symbol | Min | Max | Min | Max | |
| Α | 1.050 | 1.250 | 0.041 | 0.049 | |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 | |
| b | 0.300 | 0.500 | 0.012 | 0.020 | |
| С | 0.100 | 0.200 | 0.004 | 0.008 | |
| D | 2.820 | 3.020 | 0.111 | 0.119 | |
| E | 1.500 | 1.700 | 0.059 | 0.067 | |
| E1 | 2.650 | 2.950 | 0.104 | 0.116 | |
| е | 0.950(BSC) | | 0.037(BSC) | | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 | |
| L | 0.300 | 0.600 | 0.012 | 0.024 | |
| θ | 0° | 8° | 0° | 8° | |

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